BUV27

NPN Silicon Power Transistor

This device is designed for use in switching regulators and motor control.

Features

- Low Collection Emitter Saturation Voltage
- Fast Switching Speed
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Sustaining Voltage	V _{CEO}	120	Vdc
Collector–Emitter Breakdown Voltage	V _{CBO}	240	Vdc
Emitter-Base Voltage	V _{EBO}	7.0	Vdc
Collector Current - Continuous	I _C	12	Adc
Collector Current – Peak (Note 1)	I _{CM}	20	Adc
Base Current	I _B	4.0	Adc
Total Device Dissipation (T _C = 25°C) Derate above 25°C	P _D	70 0.56	W/°C
Operating and Storage Temperature	T _J , T _{stg}	- 65 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	1.78 62.5	°C/W

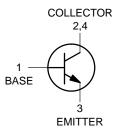


ON Semiconductor®

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POWER TRANSISTOR 12 AMPERES **120 VOLTS** 70 WATTS

SCHEMATIC



DIAGRAM

TO-220 **CASE 221A** STYLE 1



MARKING

BUV27 = Device Code

= Assembly Location

= Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BUV27G	TO-220 (Pb-Free)	50 per Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
I _{CER}	Collector Cut–off Current (R _{BE} = 50 Ω)	V _{CE} = 240 V, T _C = 125°C			3.0	mA
I _{CEX}	Collector Cut-off Current	V _{CE} = 240 V, V _{BE} = -1.5 V, T _C = 125°C			1.0	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{BE} = 5 V			1.0	mA
V _{CEO(sus)}	Collector–Emitter Sustaining Voltage	I _C = 0.2 A, L = 25 mH	120			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 50 mA	7.0		30	V
V _{CE(sat)} (Note 2)	Collector–Emitter Saturation Voltage	I _C = 4 A, I _B = 0.4 A I _C = 8 A, I _B = 0.8 A			0.7 1.5	V
V _{BE(sat)} (Note 2)	Base–Emitter Saturation Voltage	I _C = 8 A, I _B = 0.8 A			2.0	V
Resistive L	oad					
t _{on} t _s t _f	Turn-on Time Storage Time Fall Time	$V_{CC} = 90 \text{ V, } I_{C} = 8 \text{ A}$ $V_{BE} = -6 \text{ V, } I_{B1} = 0.8 \text{ A}$ $R_{BB} = 3.75 \Omega$		0.4 0.5 0.12	0.8 1.2 0.25	ms μs μs
Inductive Load						
t _s t _f	Storage Time Fall Time	$V_{CC} = 90 \text{ V, } I_{C} = 8 \text{ A}$ $I_{B1} = 0.8 \text{ A, } V_{BE} = -5 \text{ V}$ $L_{R} = 1 \mu \text{H}$		0.6 0.04		μS
t _s t _f	Storage Time Fall Time	$V_{CC} = 90 \text{ V}, I_{C} = 8 \text{ A}$ $I_{B1} = 0.8 \text{ A}, V_{BE} = -5 \text{ V}$ $L_{B} = 1 \mu\text{H}, T_{J} = 125^{\circ}\text{C}$			2.0 0.15	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulsed: Pulse Duration = $300 \mu s$, Duty Cycle = 2%

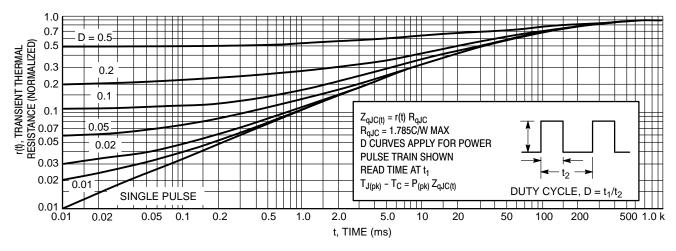
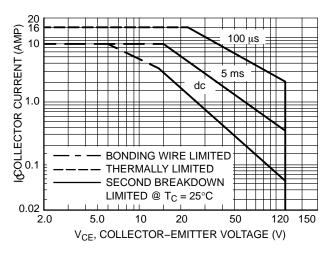


Figure 1. Thermal Response



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figures 2 is based on $T_{J(pk)}=150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)}$ < 150°C. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Figure 2. Forward Bias Safe Operating Area

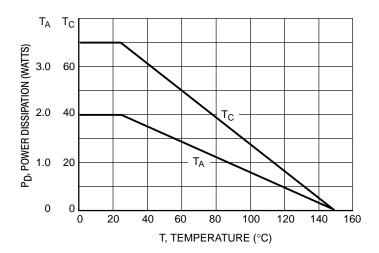
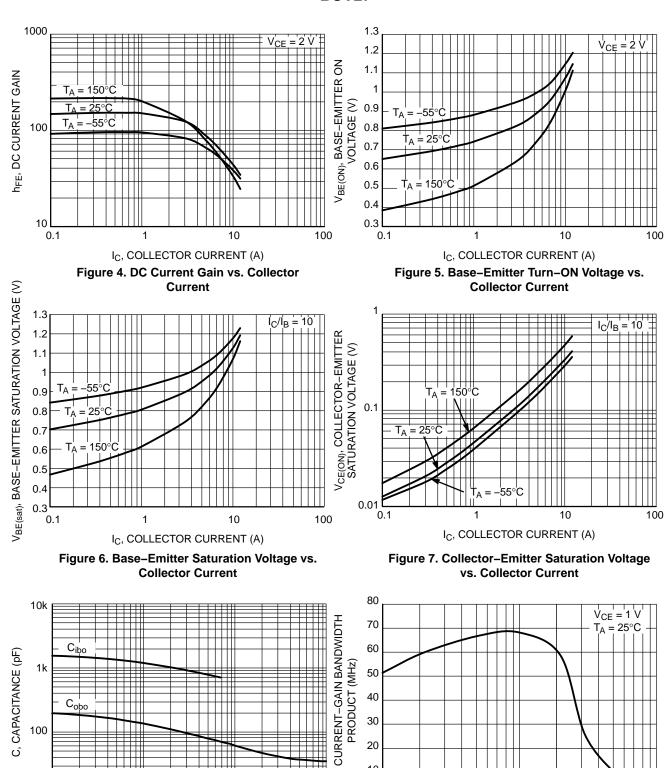


Figure 3. Power Derating



I_C, COLLECTOR CURRENT (A) Figure 9. Current Gain Bandwidth Product vs. **Collector Current**

1

10

100

10

1

V_R, REVERSE VOLTAGE (V) Figure 8. Capacitance

10

0.1

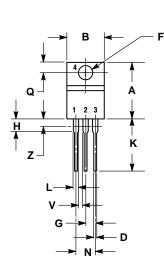
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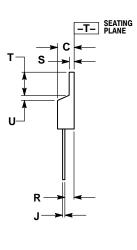
> 0 0.1

BUV27

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AH





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

PIN 1. BASE

2. COLLECTOR

3. EMITTER

4. COLLECTOR

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